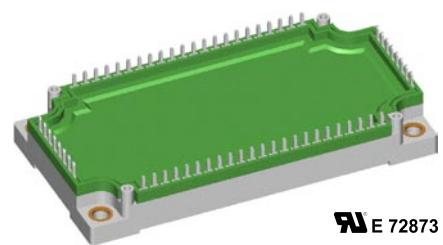
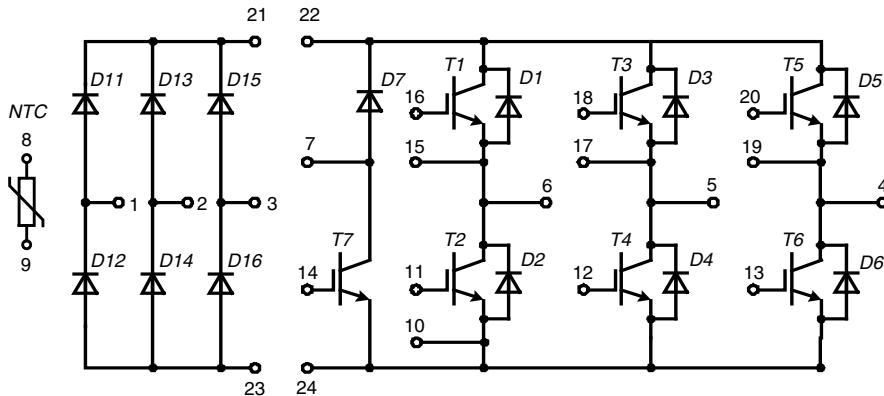


Converter - Brake - Inverter Module (CBI3) with Trench IGBT technology



Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{FAVM} = 50 \text{ A}$	$I_{C25} = 55 \text{ A}$	$I_{C25} = 80 \text{ A}$
$I_{FSM} = 850 \text{ A}$	$V_{CE(sat)} = 1.7 \text{ V}$	$V_{CE(sat)} = 1.7 \text{ V}$

Input Rectifier Bridge D11 - D16

Symbol	Conditions	Maximum Ratings		
V_{RRM}		1600	V	
I_{FAV}	$T_c = 80^\circ\text{C}$; sine 180°	50	A	
I_{DAVM}	$T_c = 80^\circ\text{C}$; rectangular; $d = 1/3$; bridge	140	A	
I_{FSM}	$T_c = 25^\circ\text{C}$; $t = 10 \text{ ms}$; sine 50 Hz	850	A	
P_{tot}	$T_c = 25^\circ\text{C}$	125	W	

Symbol Conditions

Characteristic Values

($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Conditions		min.	typ.	max.	
V_F	$I_F = 50 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			1.15 1.05	1.3	V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			0.8	0.05 mA mA	K/W
R_{thJC}	(per diode)				1.0	

Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- electric braking operation

Features

- High level of integration - only one power semiconductor module required for the whole drive
- IGBT technology with low saturation voltage, low switching losses and tail current, high RBSOA and short circuit ruggedness
- Epitaxial free wheeling diodes with Hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
V_{GES}	Continuous	± 20		V
I_{C25}	$T_C = 25^\circ\text{C}$	80		A
I_{C80}	$T_C = 80^\circ\text{C}$	50		A
I_{CM}	$T_C = 80^\circ\text{C}; t_p = 1 \text{ ms}$	100		A
P_{tot}	$T_C = 25^\circ\text{C}$	270		W

Symbol Conditions Characteristic Values(T_{VJ} = 25°C, unless otherwise specified)

			min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 50 \text{ A}; V_{GE} = 15 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.7 2.0	2.15	V
$V_{GE(th)}$	$I_C = 2 \text{ mA}; V_{GE} = V_{CE}$		5	5.8	6.5	V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			2.7 0.7	mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$				400	nA
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$			3.5		nF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 50 \text{ A}$			470		nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 50 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega$			90 50 520 90 5 6.5		ns ns ns ns mJ mJ
RBSOA		$I_C = I_{CM}; V_{GE} = 15 \text{ V}$ $R_G = 18 \Omega; T_{VJ} = 125^\circ\text{C}$		$V_{CEK} \leq V_{CES} - L_S di/dt$		V
t_{sc} (SCSOA)		$V_{CE} = 720 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega$ $t_p \leq 10 \mu\text{s}; \text{non-repetitive}; T_{VJ} = 125^\circ\text{C}$		200		A
R_{thJC}					0.46	K/W

Output Inverter D1 - D6

Symbol	Conditions	Maximum Ratings		
I_{F25}	$T_C = 25^\circ\text{C}$	100		A
I_{F80}	$T_C = 80^\circ\text{C}$	50		A

Symbol Conditions Characteristic Values

			min.	typ.	max.	
V_F	$I_F = 50 \text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			2.1 1.6	2.6	V
I_{RM} Q_{rr} t_{rr} E_{rec}	$I_F = 60 \text{ A}; di_F/dt = -1200 \text{ A}/\mu\text{s};$ $T_{VJ} = 125^\circ\text{C}; V_R = 600 \text{ V}; V_{GE} = 0 \text{ V}$			90 10 160 4		A μC ns mJ
R_{thJC}		(per diode)			0.65	K/W

Brake Chopper T7

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
V_{GES}	Continuous	± 20		V
I_{C25}	$T_C = 25^\circ\text{C}$	55		A
I_{C80}	$T_C = 80^\circ\text{C}$	35		A
I_{CM}	$T_C = 80^\circ\text{C}; t_p = 1 \text{ ms}$	70		A
P_{tot}	$T_C = 25^\circ\text{C}$	200		W

Symbol Conditions Characteristic Values(T_{VJ} = 25°C, unless otherwise specified)

			min.	typ.	max.	
$V_{CE(\text{sat})}$	$I_C = 35 \text{ A}; V_{GE} = 15 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.7 2.0	2.15	V
$V_{GE(\text{th})}$	$I_C = 1.5 \text{ mA}; V_{GE} = V_{CE}$		5	5.8	6.5	V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			0.25 0.3	mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$				400	nA
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$			2.5		nF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 35 \text{ A}$			330		nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 35 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 27 \Omega$			90 50 520 90 4.8		ns ns ns ns mJ
RBSOA		$I_C = I_{CM}; V_{GE} = 15 \text{ V}$ $R_G = 27 \Omega; T_{VJ} = 125^\circ\text{C}$	$V_{CEK} \leq V_{CES} - L_S \frac{di}{dt}$			V
t_{sc} (SCSOA)		$V_{CE} = 720 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 27 \Omega$ $t_p \leq 10 \mu\text{s}; \text{non-repetitive}; T_{VJ} = 125^\circ\text{C}$		140		A
R_{thJC}					0.62	K/W

Brake Chopper D7

Symbol	Conditions	Maximum Ratings		
V_{RRM}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
I_{F25}	$T_C = 25^\circ\text{C}$	48		A
I_{F80}	$T_C = 80^\circ\text{C}$	30		A

Symbol Conditions Characteristic Values

			min.	typ.	max.	
V_F	$I_F = 35 \text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			2.5 2.0	3.3	V
I_R	$V_R = V_{RRM}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$				0.25 0.5	mA mA
R_{thJC}	(per diode)				1.2	K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ\text{C}$	4.75	5.0	5.25
$B_{25/50}$			3375	$\text{k}\Omega$ K

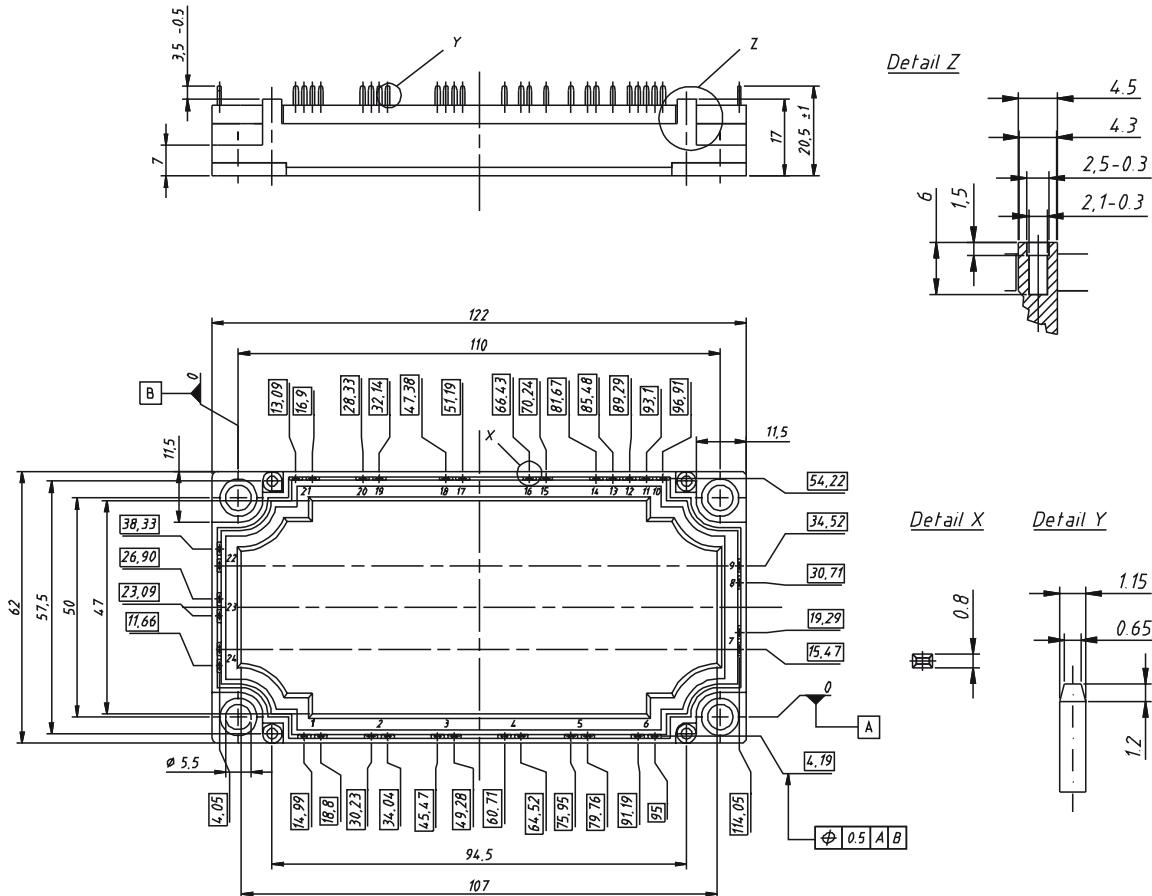
Module

Symbol	Conditions	Maximum Ratings		
T_{VJ}	operating	-40...+125	$^\circ\text{C}$	
T_{JM}		+150	$^\circ\text{C}$	
T_{stg}		-40...+125	$^\circ\text{C}$	
V_{ISO}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~	
M_d	Mounting torque (M5)	3 - 6	Nm	

Symbol Conditions

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{therm-chip}$	Resistance terminal to chip		5	$\text{m}\Omega$
d_s	Creepage distance on surface	6		mm
d_A	Strike distance in air	6		mm
R_{thCH}	with heatsink compound		0.01	K/W
Weight			300	g

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions.

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Input Rectifier Bridge D11 - D16

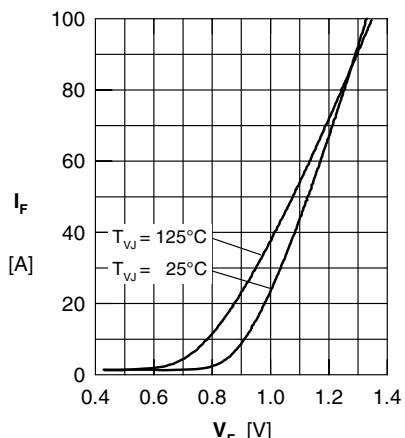


Fig. 1 Typ. forward current vs.
voltage drop per diode

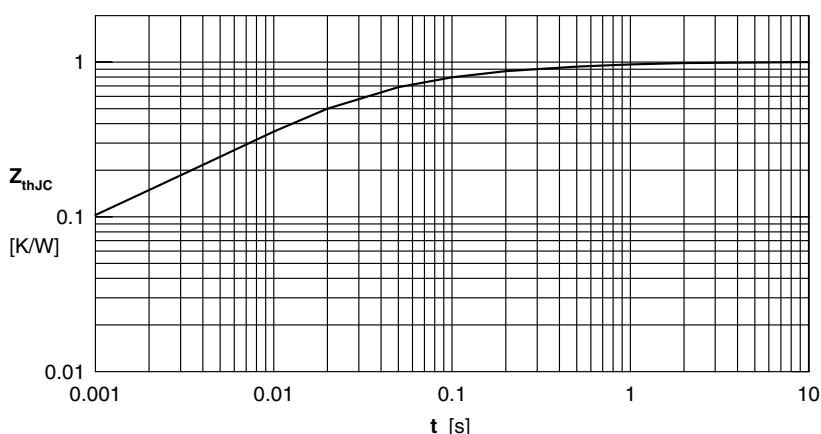


Fig. 2 Transient thermal impedance junction to case

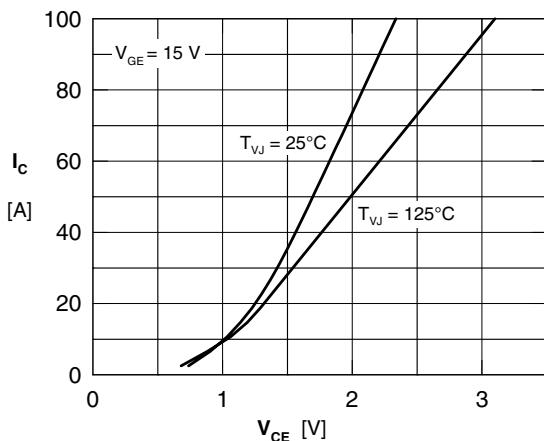
Output Inverter T1 - T6 / D1 - D6


Fig. 3 Typical output characteristic

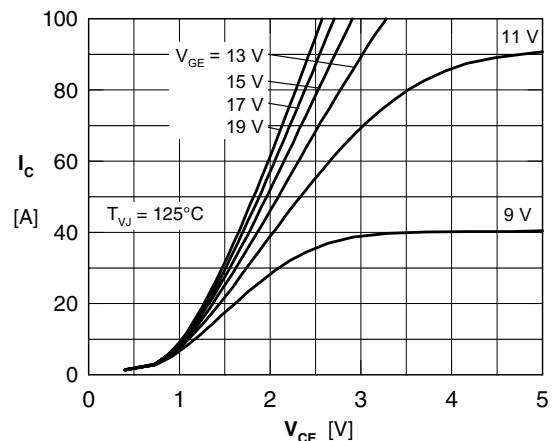


Fig. 4 Typical output characteristic

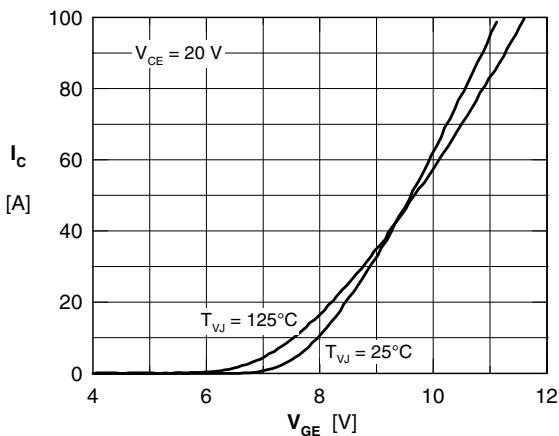


Fig. 5 Typical transfer characteristic

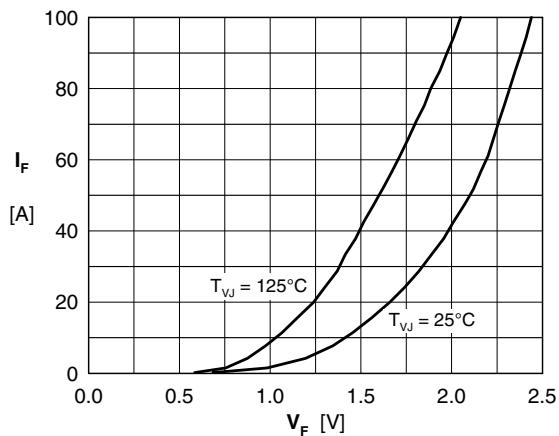


Fig. 6 Typical forward characteristic of free wheeling diode

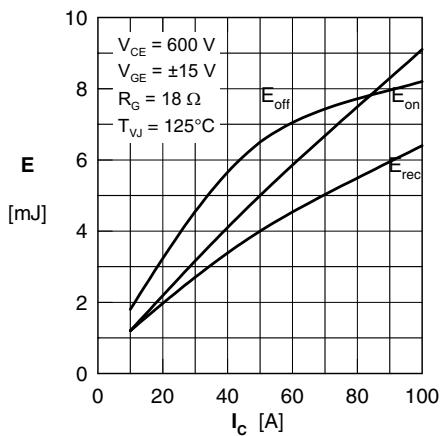


Fig. 7 Typ. switching losses vs. collector current

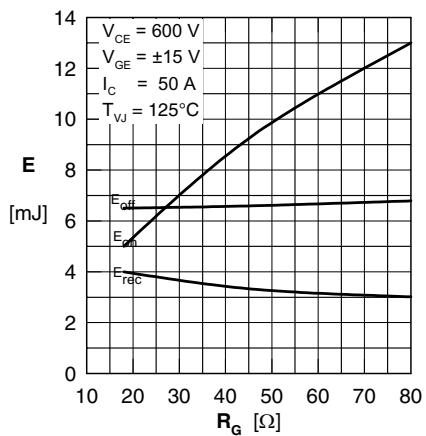


Fig. 8 Typ. switching losses vs. gate resistance

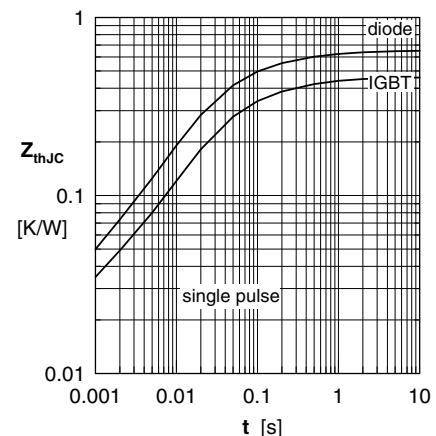


Fig. 9 Transient thermal impedance